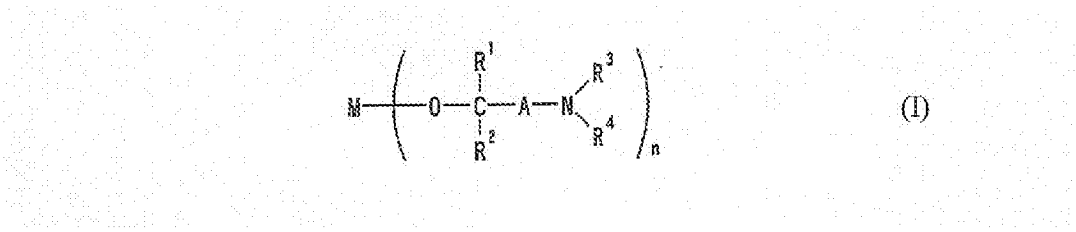
AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (currently amended) A metal compound represented by general formula (I):



(I)

wherein R^1, R^2, R^3, and R^4 each represent an alkyl group having 1 to 4 carbon atoms; A represents ~~an alkanediyl group having 1 to 8 carbon atoms~~ a methylene group; M represents ~~a lead atom,~~ a titanium atom or a zirconium atom; and n represents ~~2 when M is a lead atom or~~ 4 ~~when M is a titanium or zirconium atom~~.

2. (canceled)

3. (canceled)

4. (currently amended) The metal compound according to claim 1, wherein M is [[a]] the titanium atom.

5. (currently amended) The metal compound according to claim 1, wherein M is [[a]] the zirconium atom.

6. (previously presented) A material for thin film formation comprising the metal compound according to claim 1.

7. (currently amended) A material for thin film formation, comprising: ~~a metal compound of formula (I), wherein M is a lead atom;~~

a compound of formula (I), wherein M is a titanium atom; and

a compound of formula (I), wherein M is a zirconium atom;

and wherein the compound of formula (I) is the compound according to claim 1.

8. (currently amended) A material for thin film formation comprising the metal compound of claim [[3]] 1, tetrakis(1-methoxy-2-methyl-2-propoxy)titanium, and tetrakis(1-methoxy-2-methyl-2-propoxy)zirconium.

9. (currently amended) A process for thin film formation, comprising:

vaporizing the material for thin film formation according to claim 6;[[,]]

introducing the resulting vapor containing the metal compound onto a substrate;[[,]] and

causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

10. (currently amended) A process for thin film formation comprising:

vaporizing a material for thin film formation containing the metal compound of claim [[3]] 1, to obtain vapor containing the metal ~~compounds~~ compound;[[,]]

introducing the resulting vapor containing the metal compounds onto a substrate;[[,]] and

causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

11. (currently amended) A process for thin film formation, comprising:

vaporizing a material for thin film formation containing the metal compound of claim [[3]] 1, a material for thin film formation containing tetrakis(1-methoxy-2-methyl-2-propoxy)titanium, and a material for thin film formation containing tetrakis(1-methoxy-2-methyl-2-propoxy)zirconium to obtain vapor containing the metal compounds;[[,]]

introducing the resulting vapor containing the metal compounds onto a substrate;[[,]] and

causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

12. (currently amended) A process for thin film formation comprising

vaporizing a material for thin film formation containing the metal compound of claim [[3]] 1, a material for thin film formation containing tetra(tert-butoxy)titanium, and a material for thin film formation containing tetra(tert-butoxy)zirconium to obtain vapor containing the metal compounds;[[,]]

introducing the resulting vapor containing the metal compounds onto a substrate;[[,]] and

causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

13. (currently amended) A process for thin film formation, comprising:

vaporizing a material for thin film formation containing the metal compound of claim 4, to obtain vapor containing the metal compounds;[[,]]

introducing the resulting vapor containing the metal compounds onto a substrate;[[,]] and

causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

14. (currently amended) A process for thin film formation, comprising:

vaporizing a material for thin film formation containing the metal compound of claim 5, to obtain vapor containing the metal compounds;[[,]]

introducing the resulting vapor containing the metal compounds onto a substrate;[[,]] and

causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

15. (currently amended) A process for thin film formation, comprising:

vaporizing the material for thin film formation according to claim 7;[[,]]

introducing the resulting vapor containing the metal compound onto a substrate;[[,]] and

causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

16. (currently amended) A process for thin film formation, comprising:

vaporizing the material for thin film formation according to claim 8;[[,]]

introducing the resulting vapor containing the metal compound onto a substrate;[[,]] and

causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

17. (canceled)

18. (canceled)

19. (canceled)